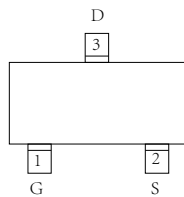


- ◆ N-Channel Power MOS FET
- ◆ DMOS Structure
- ◆ Low On-State Resistance : 0.1Ω (max)
- ◆ Ultra High-Speed Switching
- ◆ Gate Protect Diode Built-in
- ◆ SOT - 23 Package

■ General Description

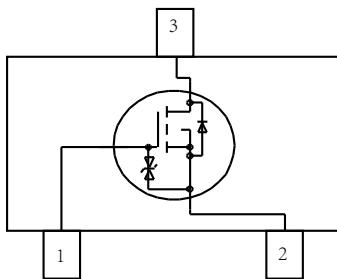
The SI2306A0MR is a N-Channel Power MOS FET with low on state resistance and ultra high-speed switching characteristics. Because high-speed switching is possible, the IC can be efficiently set thereby saving energy. In order to counter static, a gate protect diode is built-in. The small SOT-23 package makes high density mounting possible.

■ Pin Configuration



SOT - 23 Top View

■ Equivalent Circuit



N - Channel MOS FET
(1 device built-in)

- Applications
- ? Notebook PCs
- ? Cellular and portable phones
- ? On - board power supplies
- ? Li - ion battery systems

■ Features

Low on-state resistance : $R_{ds(on)} = 0.1\Omega$ ($V_{gs} = 4.5V$)
 $R_{ds(on)} = 0.14\Omega$ ($V_{gs} = 2.5V$)
 $R_{ds(on)} = 0.25\Omega$ ($V_{gs} = 1.5V$)
 Ultra high-speed switching
 Gate Protect Diode Built-in
 Operational Voltage : 1.5V
 High density mounting : SOT - 23

■ Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1	G	Gate
2	S	Source
3	D	Drain

■ Absolute Maximum Ratings

$T_a = 25^\circ C$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain - Source Voltage	V_{dss}	20V	
Gate - Source Voltage	V_{gss}	± 8	V
Drain Current (DC)	I_d	1	A
Drain Current (Pulse)	I_{dp}	4	A
Reverse Drain Current	I_{dr}	1	A
Continuous Channel Power Dissipation (note)	P_d	0.5	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

(note) : When implemented on a ceramic PCB

■ □ Electrical Characteristics

DC characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds = 20, Vgs = 0V			10	∞A
Gate-Source Leakage Current	Igss	Vgs = ± 8, Vds = 0V			± 10	∞A
Gate-Source Cut-off Voltage	Vgs (off)	Id = 1mA, Vds = 10V	0.5		1.2	V
Drain-Source On-state Resistance (note)	Rds (on)	Id = 0.5A, Vgs = 4.5V		0.075	0.1	Ω
		Id = 0.5A, Vgs = 2.5V		0.1	0.14	Ω
		Id = 0.1A, Vgs = 1.5V		0.17	0.25	Ω
Forward Transfer Admittance (note)	Yfs	Id = 0.5A, Vds = 10V		4.2		S
Body Drain Diode Forward Voltage	Vf	If = 1A, Vgs = 0V		0.8	1.1	V

(note) : Effective during pulse test.

Dynamic characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds = 10V, Vgs = 0V f = 1 MHz		220pF		
Output Capacitance	Coss			120		pF
Feedback Capacitance	Crss			45		pF

Switching characteristics

Ta=25°C

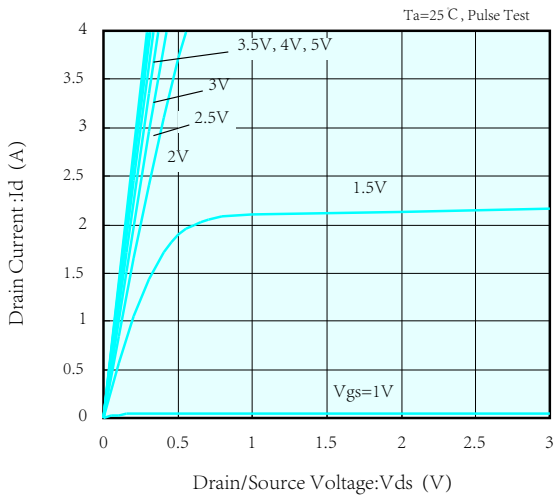
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	td (on)	Vgs = 5V, Id = 0.5A Vdd = 10V		10ns		
Rise Time	tr			15		ns
Turn-off Delay Time	td (off)			75		ns
Fall Time	tf			65		ns

Thermal characteristics

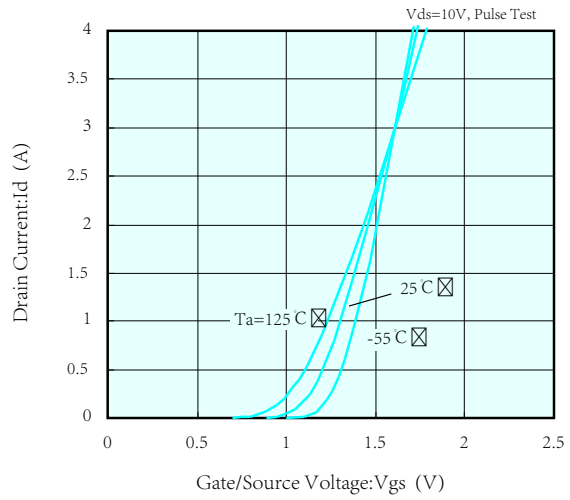
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel - surroundings)	Rth (ch - a)	Implement on a ceramic PCB		250		°C/W

■ XP151A13A0MR Electrical Characteristics

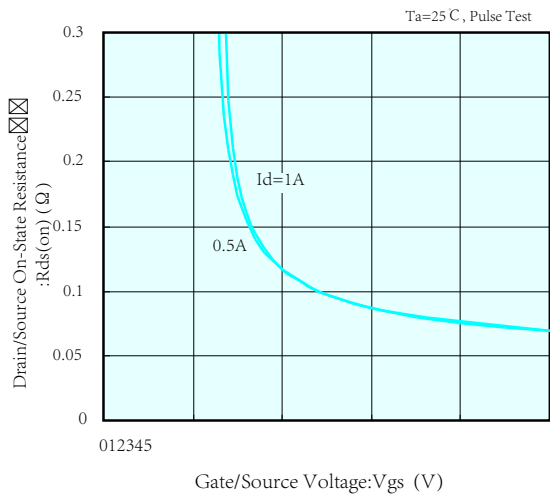
Drain Current vs. Drain/Source Voltage



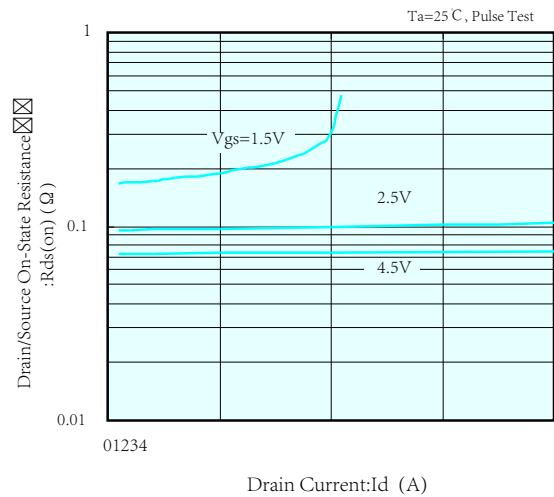
Drain Current vs. Gate/Source Voltage



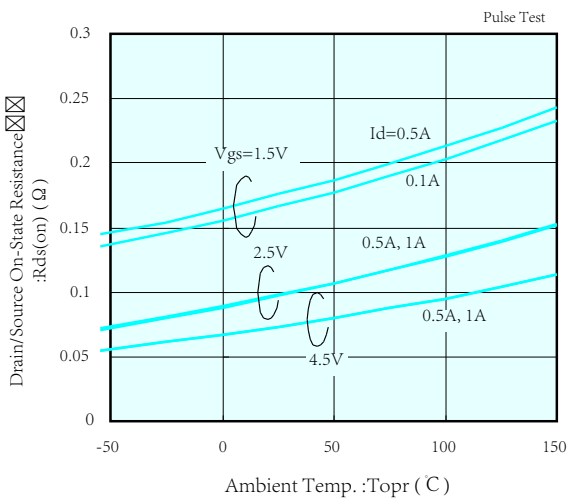
Drain/Source On-State Resistance vs. Gate/Source Voltage



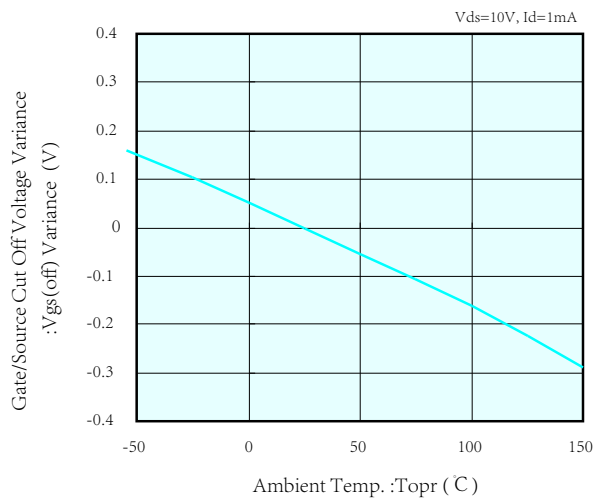
Drain/Source On-State Resistance vs. Drain Current



Drain/Source On-State Resistance vs. Ambient Temp.

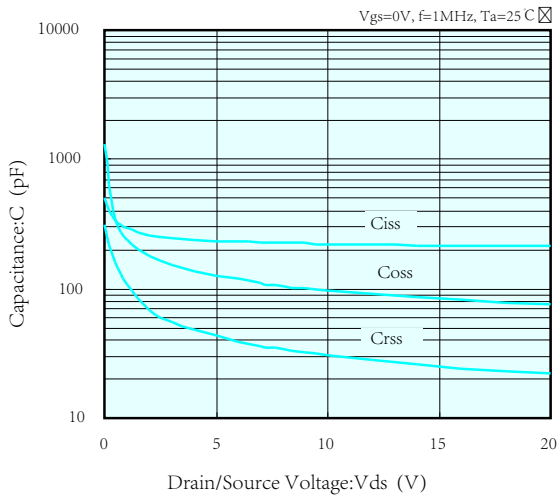


Gate/Source Cut Off Voltage Variance vs. Ambient Temp.

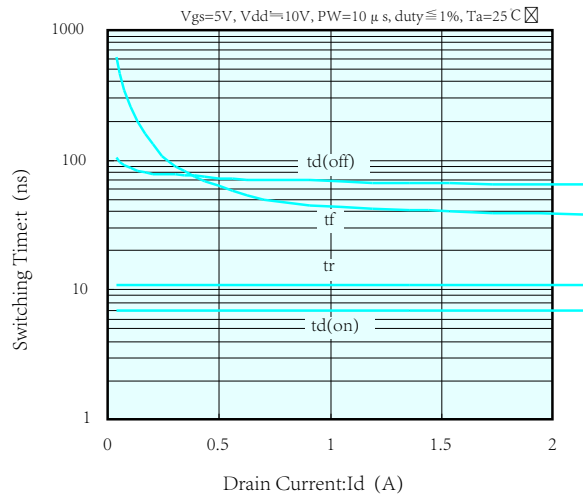


■ SI2306A0MR Electrical Characteristics

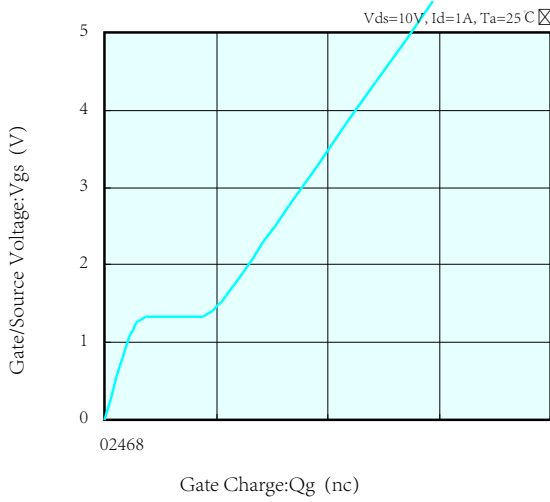
Capacitance vs. Drain/Source Voltage



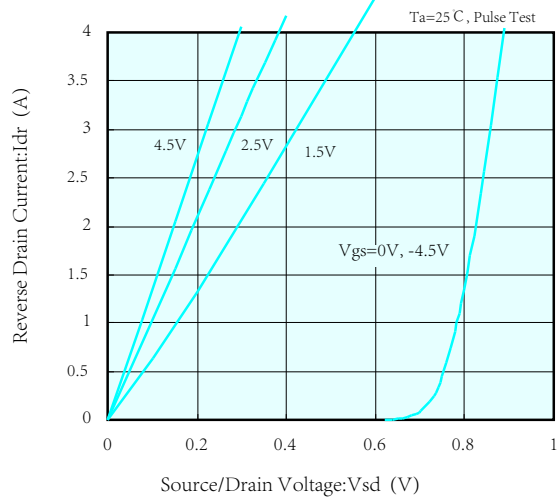
Switching Time vs. Drain Current



Gate/Source Voltage vs. Gate Charge



Reverse Drain Current vs. Source/Drain Voltage



Standardized Transition Thermal Resistance vs. Pulse Width

